P-Channel Enhancement-Mode Vertical DMOS FET

Features

- Low threshold (-2.0V max.)
- High input impedance
- Low input capacitance
- Fast switching speeds
- Low on-resistance
- Free from secondary breakdown
- Low input and output leakage
- Complementary N- and P-channel devices

Applications

- Logic level interfaces - ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

General Description

This low threshold enhancement-mode (normally-off) transistor utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package Option	BV_{DSS}/BV_{DGS} (max) (V)	$R_{DS(ON)}$ (max) (Ω)	$V_{GS(th)}$ (max) (V)	$I_{D(ON)}$ (min) (A)
	TO-92				
TP2635	TP2635N3-G	-350	15	-2.0	-0.7

-G indicates package is RoHS compliant ('Green')

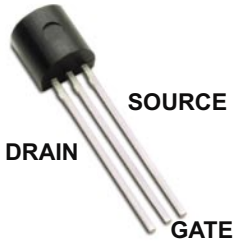
Absolute Maximum Ratings

Parameter	Value
Drain-to-source voltage	BV_{DSS}
Drain-to-gate voltage	BV_{DGS}
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

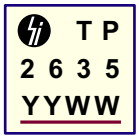
* *Distance of 1.6mm from case for 10 seconds.*

Pin Configuration



TO-92 (N3)

Product Marking



YY = Year Sealed
WW = Week Sealed
_____ = "Green" Packaging

TO-92 (N3)

Thermal Characteristics

Package	I_D (continuous)† (mA)	I_D (pulsed) (A)	Power Dissipation @T_C = 25°C (W)	θ_{jc} (°C/W)	θ_{ja} (°C/W)	I_{DR}† (mA)	I_{DRM} (A)
TO-92	-180	-0.8	1.0	125	170	-180	-0.8

Notes:

† *I_D (continuous) is limited by max rated T_j.*

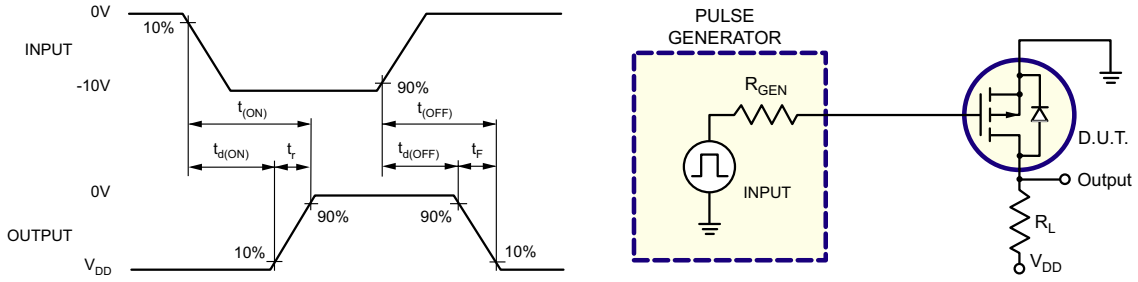
Electrical Characteristics *(T_A = 25°C unless otherwise specified)*

Sym	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	-350	-	-	V	V_{GS} = 0V, I_D = -2.0mA
$V_{GS(th)}$	Gate threshold voltage	-0.8	-	-2.0	V	V_{GS} = V_{DS}, I_D = -1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-	5	mV/°C	V_{GS} = V_{DS}, I_D = -1.0mA
I_{GSS}	Gate body leakage	-		-100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero gate voltage drain current	-	-	-1.0	μA	V_{GS} = 0V, V_{DS} = -100V
				-10.0		V_{GS} = 0V, V_{DS} = Max rating
				-1.0	mA	V_{DS} = 0.8 Max Rating, V_{GS} = 0V, T_A = 125°C
$I_{D(ON)}$	On-state drain current	0.7	-	-	A	V_{GS} = -10V, V_{DS} = -25V
$R_{DS(ON)}$	Static drain-to-source on-state resistance	-	12	15	Ω	V_{GS} = -2.5V, I_D = -20mA
			11	15		V_{GS} = -4.5V, I_D = -150mA
			11	15		V_{GS} = -10V, I_D = -300mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	-	0.75	%/°C	V_{GS} = -10V, I_D = -300mA
G_{FS}	Forward transconductance	200	-	-	mmho	V_{DS} = -25V, I_D = -300mA
C_{ISS}	Input capacitance	-	-	300	pF	V_{GS} = 0V, V_{DS} = -25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	-	50		
C_{RSS}	Reverse transfer capacitance	-	-	12		
$t_{d(ON)}$	Turn-on delay time	-	-	10	ns	V_{DD} = -25V, I_D = -300MA, R_{GEN} = 25Ω
t_r	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-off delay time	-	-	60		
t_f	Fall time	-	-	40		
V_{SD}	Diode forward voltage drop	-	-	-1.8	V	V_{GS} = 0V, I_{SD} = -200mA
t_{rr}	Reverse recovery time	-	300	-	ns	V_{GS} = 0V, I_{SD} = -200mA

Notes:

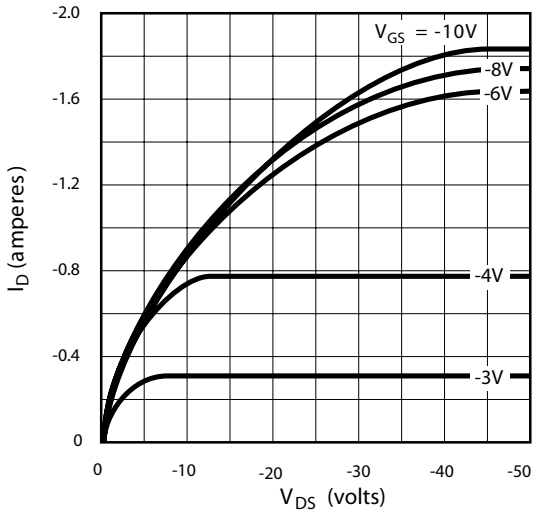
1. *All D.C. parameters 100% tested at 25C unless otherwise stated. (Pulse test: 300s pulse, 2% duty cycle.)*
2. *All A.C. parameters sample tested.*

N- Channel Switching Waveforms and Test Circuit

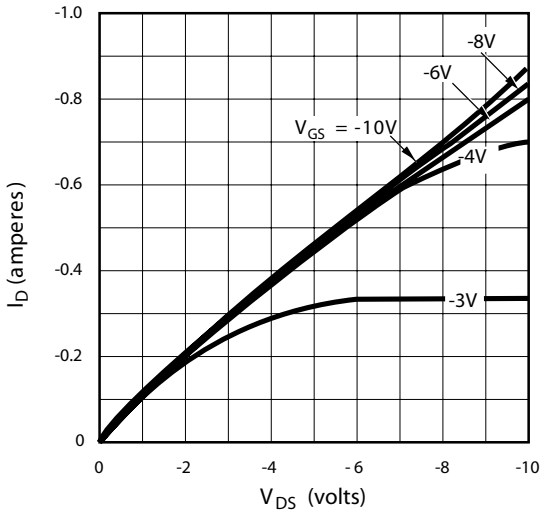


Typical Performance Curves

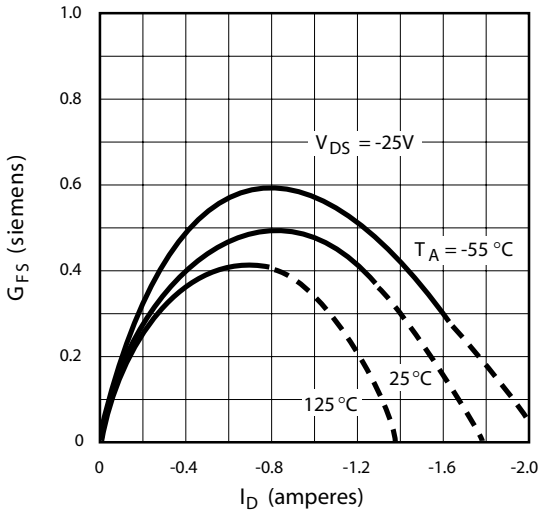
Output Characteristics



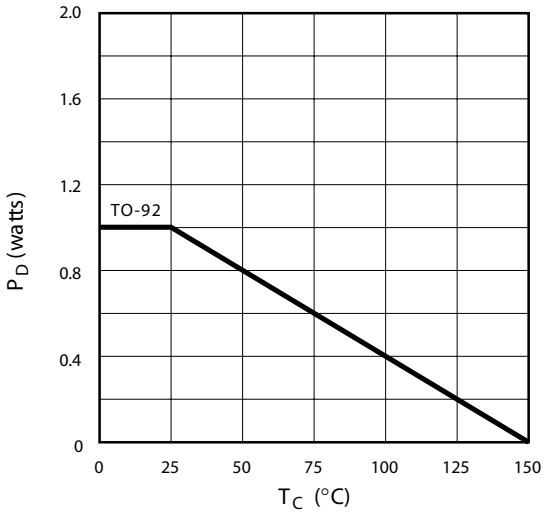
Saturation Characteristics



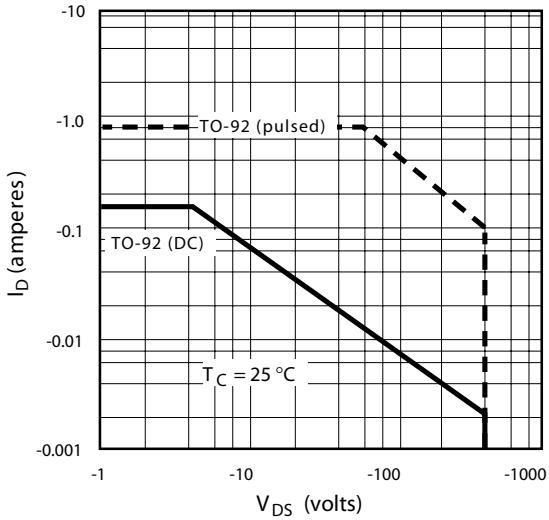
Transconductance vs. Drain Current



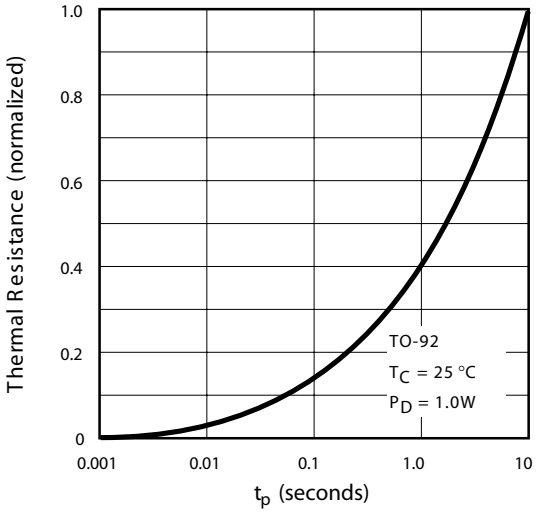
Power Dissipation vs. Temperature



Maximum Rated Safe Operating Area

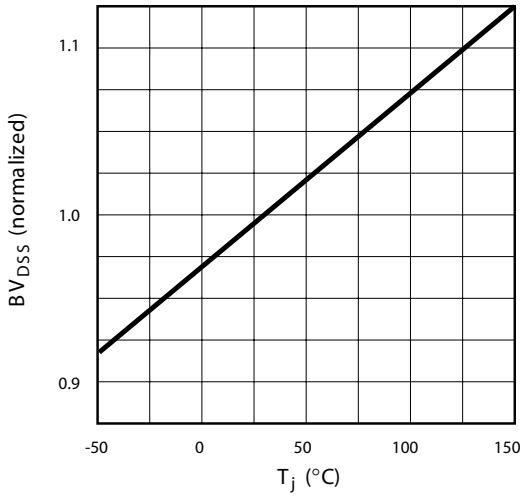


Thermal Response Characteristics

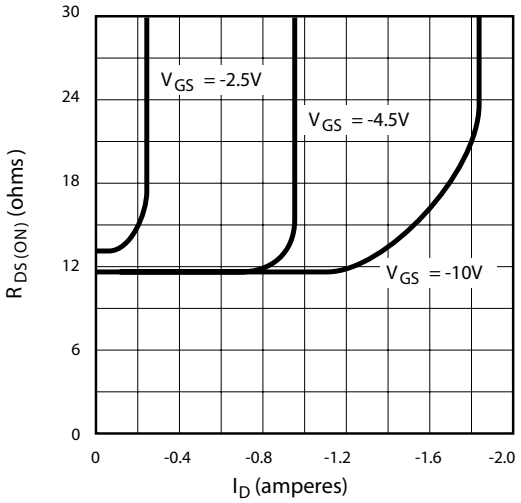


Typical Performance Curves (cont.)

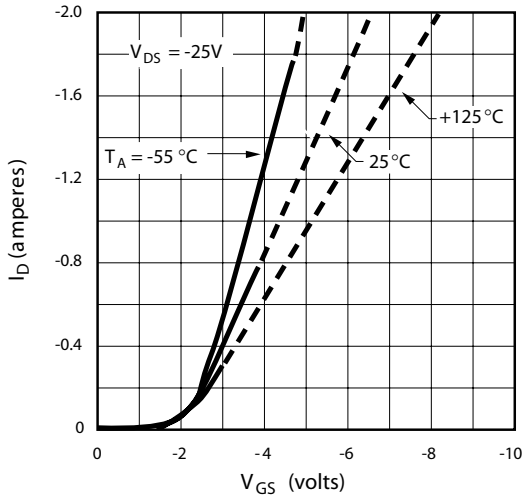
BV $_{DSS}$ Variation with Temperature



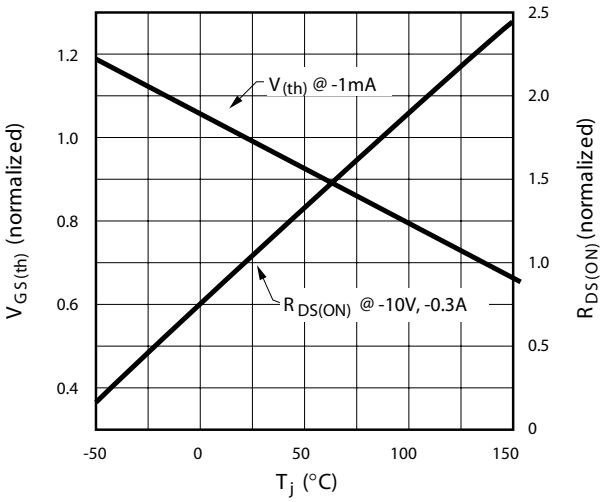
On-Resistance vs. Drain Current



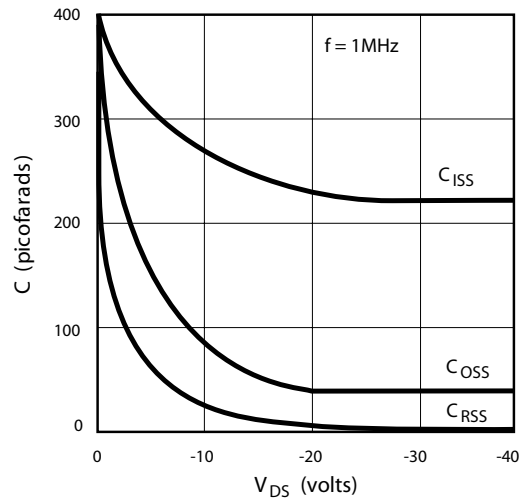
Transfer Characteristics



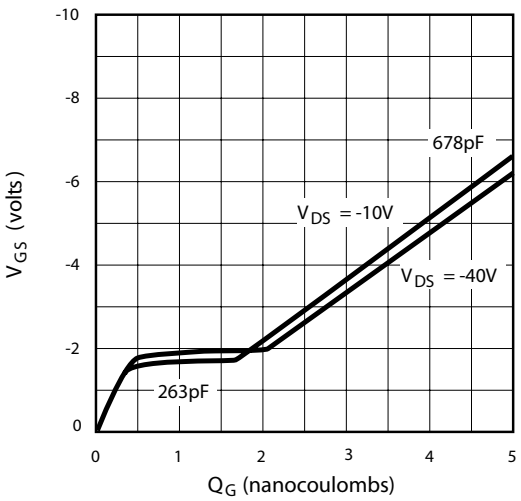
V_{TH} and R $_{DS}$ Variation with Temperature



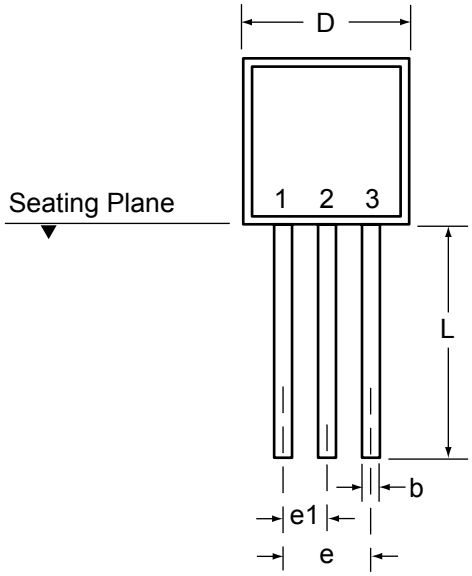
Capacitance vs. Drain-to-Source Voltage



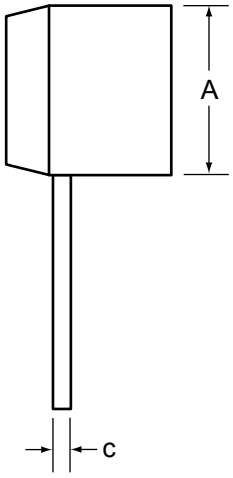
Gate Drive Dynamic Characteristics



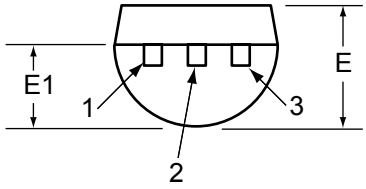
3-Lead TO-92 Package Outline (N3)



Front View



Side View



Bottom View

Symbol		A	b	c	D	E	E1	e	e1	L
Dimensions (inches)	MIN	.170	.014†	.014†	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.
** This dimension is not specified in the original JEDEC drawing. The value listed is for reference only.*
† This dimension is a non-JEDEC dimension.
Drawings not to scale.
***Supertex Doc.#:** DSPD-3TO92N3, Version D080408.*

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

Supertex inc.
1235 Bordeaux Drive, Sunnyvale, CA 94089
Tel: 408-222-8888
www.supertex.com